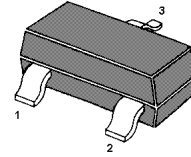


PNP Silicon Epitaxial Planar Transistor

for low frequency power amplifier and power switching applications

The transistor is subdivided into two groups, O and Y according to its DC current gain.



1.Base 2.Emmitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

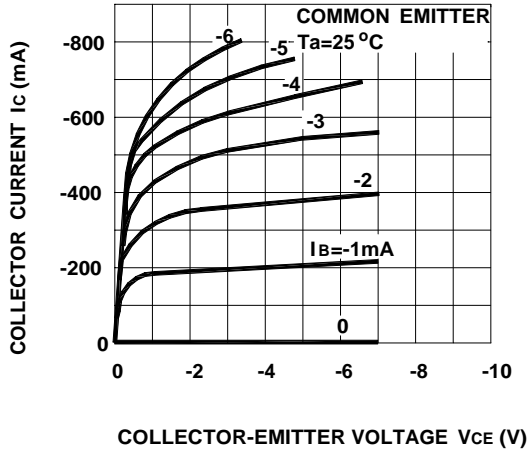
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	30	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	800	mA
Base Current	$-I_B$	160	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Characteristics at $T_{amb}=25\text{ }^\circ\text{C}$

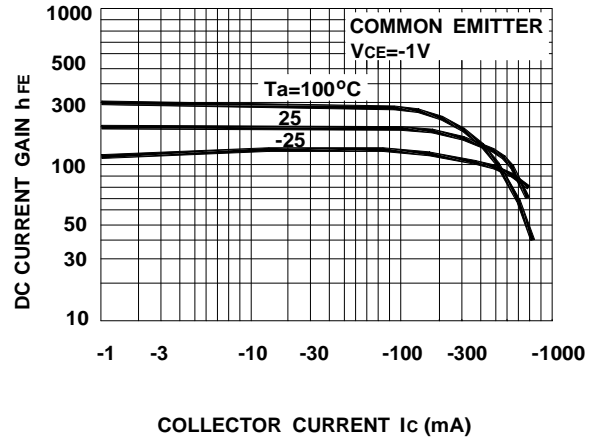
Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	O	h_{FE}	100	-	200	-
		h_{FE}	160	-	320	-
	Y	h_{FE}	40	-	-	-
at $-V_{CE} = 1\text{ V}$, $-I_C = 800\text{ mA}$						
Collector Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CB0}$	-	-	0.1	μA	
Emitter Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	0.1	μA	
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 20\text{ mA}$	$-V_{CE(sat)}$	-	-	0.4	V	
Base Emitter Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 10\text{ mA}$	$-V_{BE}$	0.5	-	0.8	V	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 0.1\text{ mA}$	$-V_{(BR)EBO}$	5	-	-	V	
Transition Frequency at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	f_T	-	120	-	MHz	
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	13	-	pF	



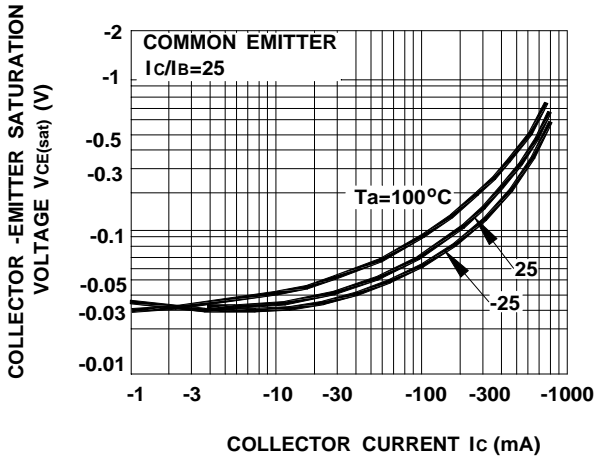
Ic - VCE



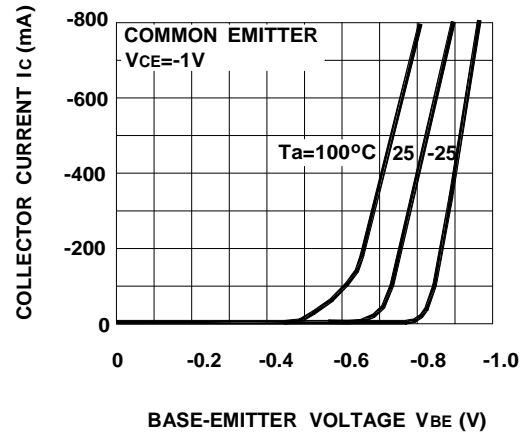
hFE - IC



VCE(sat) - IC



Ic - VBE



Pc - Ta

